

# Contents

PREFACE	xv
ACKNOWLEDGMENTS	xvii
MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS	xviii
PART I: ION-BEAM ASSISTED DEPOSITION	
*SOME RECENT RESULTS OF FUNDAMENTAL STUDIES ON BEAM-INDUCED SURFACE PROCESSES Jan Dieleman	3
STRESS MODIFICATION IN TUNGSTEN FILMS DEPOSITED BY ION-ASSISTED EVAPORATION R.A. Roy, R. Petkie, D.S. Yee, J. Karasinski, and A. Boulding	17
CONTROL OF METAL FILM PROPERTIES BY ION ASSISTED DEPOSITION Ronnen A. Roy, Dennis S. Yee, and Jerome J. Cuomo	23
SOFT MAGNETISM AND MORPHOLOGY OF Fe FILMS BY DUAL ION BEAM SPUTTERING M. Nagakubo, T. Yamamoto, and M. Naoe	29
ARGON ION BOMBARDMENT DURING MOLECULAR BEAM EPITAXY OF Ge (001) Eric Chason, K.M. Horn, J.Y. Tsao, and S.T. Picraux	35
EFFECTS OF SPUTTERED PARTICLE ENERGY ON THE PROPERTIES OF SiO <sub>2</sub> FILMS Yasunori Taga and Takeshi Ohwaki	41
METAL SILICIDES FORMED BY DIRECT ION BEAM DEPOSITION R.A. Zuhr, S.J. Pennycook, T.E. Haynes, and O.W. Holland	47
ION BEAM ASSISTED DEPOSITION OF TITANIUM NITRIDE G.K. Hubler, D. Van Vechten, E.P. Donovan, and R.A. Kant	55
PROPERTIES OF SILICON OXYNITRIDE AND ALUMINUM OXYNITRIDE COATINGS DEPOSITED USING ION ASSISTED DEPOSITION G.A. Al-Jumaily, T.A. Mooney, W.A. Spurgeon, and H.M. Dauplaise	61
PLASMA-ACTIVATED ION BEAM REACTIVE SPUTTERING OF NbN THIN FILMS D.J. Lichtenwalner, Alfredo C. Anderson, and D.A. Rudman	67

\*Invited Paper

INVESTIGATION OF TITANIUM NITRIDE SYNTHESIZED BY ION BEAM ENHANCED DEPOSITION	73
Zhou Jiankun, Liu Xianghuai, Chen Youshan, Zheng Zhihong, Huang Wei, Zhou Zuyao, and Zou Shichang	
$B_{(1-x)}N_x$ ALLOY FILMS PREPARED BY ION BEAM ASSISTED DEPOSITION	79
C.A. Carosella, G.K. Hubler, D. Van Vechten, and E.P. Donovan	
ANALYSIS OF NITROGEN, BORON, AND HYDROGEN OF i-BN FILMS FABRICATED BY THE ION BEAM ASSISTED DEPOSITION	85
J-P. Hirvonen and J.K. Hirvonen	
A NEW APPARATUS FOR DYNAMICAL ION BEAM MIXING	91
M. Jaulin, G. LaPlanche, J. Delafond, and S. Pimbert-Michaux	
*IN SITU PARAMETRIC INVESTIGATION OF THE MECHANISM OF DIAMOND FILM DEPOSITION FROM LOW ENERGY ION BEAMS	101
Y. Lifshitz, S.R. Kasi, and J.W. Rabalais	
ION BEAM DEPOSITION OF DIAMOND-LIKE COATINGS	109
Anton C. Greenwald, James K. Hirvonen, and Narendra K. Jaggi	
*EFFECTS OF IONIZED CLUSTER BEAM BOMBARDMENT ON EPITAXIAL METAL FILM DEPOSITION ON SILICON SUBSTRATES	113
Isao Yamada	
CLUSTER SIZE MEASUREMENTS IN AN IONIZED CLUSTER BEAM SYSTEM	125
D.E. Turner, K.M. Lakin, and H.R. Shanks	
ALUMINUM ATOM SURFACE MOBILITY ON SiO <sub>2</sub> DURING IONIZED CLUSTER BEAM DEPOSITION	131
Leonard L. Levenson, Amy B. Swartzlander, Hiroaki Usui, Isao Yamada, and Toshinori Takagi	
*ATOMIC-SCALE MODELING OF LOW-ENERGY ION-SOLID PROCESSES	137
Brian W. Dodson	
COLLISION CASCADE DENSIFICATION OF MATERIALS	151
R.H. Bassel, T.D. Andreadis, M. Rosen, G.P. Mueller, and G.K. Hubler	
MOLECULAR DYNAMICS SIMULATIONS OF LOW ENERGY DISPLACEMENT CASCADES IN SILICON	157
A.M. Mazzone	
A THERMAL SPIKE ANALYSIS OF LOW ENERGY ION ACTIVATED SURFACE PROCESSES	163
C.M. Gilmore, A. Haeri, and J.A. Sprague	

\*Invited Paper

A MODEL OF A COMBINED FILM DEPOSITION AND ION BOMBARDMENT FOR COATINGS FORMATION Z.A. Iskanderova, T.D. Radjabov, R. Yu. Leiderman, and F.K. Tukfatullin	169
THE INFLUENCE OF DEFECT CONCENTRATIONS ON MIGRATION ENERGIES IN AgZn ALLOYS T.D. Andreadis, M. Rosen, J.M. Eridon, and D.J. Rosen	175
SUPERADDITIVITY IN THE IMPLANTATION OF MOLECULAR IONS G.F. Cerofolini, L. Meda, and C. Volpones	181
PART II: ION-BEAM MIXING	
A COMPARISON BETWEEN HIGH- AND LOW-ENERGY ION MIXING Y.-T. Cheng, E.-H. Cirlin, B.M. Clemens, and A.A. Dow	189
THERMAL SPIKE RELATED NONLINEAR EFFECTS IN ION BEAM MIXING AT LOW TEMPERATURES G-S. Chen, D. Farkas, and M. Rangaswamy	195
DIFFUSION IN IRRADIATED AgZn ALLOYS USING DEFECT-CONCENTRATION DEPENDENT MIGRATION ENERGIES T.D. Andreadis, M. Rosen, and J.M. Eridon	201
A COMPARISON OF THE MIXING RATES FOR Fe-Ti AND Ni-Ti BILAYERS P. Borgesen, D.A. Lilienfeld, R.E. Wistrom, and H.H. Johnson	207
ION-BEAM MIXING IN AMORPHOUS AND CRYSTALLINE Fe-Ti Udo Scheuer, Lynn E. Rehn, and Pete Baldo	213
THE EFFECT OF HYDROGEN CONTENT ON ION BEAM MIXING R.E. Wistrom, P. Borgesen, H.H. Johnson, and D.A. Lilienfeld	219
MAGNETIC ANOMALY AND ICOSAHEDRAL PHASE FORMATION IN Fe-Cu AND Fe-Mo SYSTEMS L.J. Huang, Q.M. Chen, B.X. Liu, Y.D. Fan, and H-D. Li	225
AMORPHOUS AND METASTABLE PHASE FORMATION IN SYSTEMS WITH POSITIVE HEATS OF MIXING USING HIGH-RATE SPUTTER DEPOSITION H.F. Rizzo, A. Echeverria, T.B. Massalski, and H. Baxi	231
MORPHOLOGY OF AMORPHOUS ALLOY FORMED BY ION BEAM BOMBARDMENT Tian Wei, Cai Wei Ping, Li Jun, and Wu Run	237
COMPOSITION- AND TEMPERATURE-DEPENDENCE OF ION MIXING IN AMORPHOUS Si/Ge ARTIFICIAL MULTILAYERS B. Park, F. Spaepen, J.M. Poate, F. Priolo, and D.C. Jacobson	243

ION BEAM INDUCED INTERMIXING OF WSi <sub>0.45</sub> ON GaAs S.J. Pearton, K.T. Short, K.S. Jones, A.G. Baca, and C.S. Wu	249
THERMALLY AND ION-INDUCED REACTIONS OF METAL WITH CuO SUBSTRATE Jian Li, S.Q. Wang, and J.W. Mayer	255
ION BEAM MIXING OF HIGH-T <sub>c</sub> SUPERCONDUCTOR COMPONENTS P. Børgeesen and D.A. Lilienfeld	261
PART III: MICROSTRUCTURAL CHANGES/CHARACTERIZATION	
*ANGLE OF INCIDENCE EFFECTS IN ION BEAM PROCESSING J.M.E. Harper, S.E. Hörnström, P.J. Rudeck, and R.M. Bradley	269
EPITAXIAL GROWTH OF Ni ON Si BY ION BEAM ASSISTED DEPOSITION K.S. Grabowski, R.A. Kant, and S.B. Qadri	279
Ge HETEROEPITAXY ON (100) Si SUBSTRATES BY ION ASSISTED DEPOSITION T.G. Holesinger, D.J. Heim, K.M. Lakin, and H.R. Shanks	285
SILICON HOMOEPITAXY AT LOW TEMPERATURE USING MICROWAVE MULTIPOLAR PLASMA FOR CLEANING AND DEPOSITION R. Burke, M. Guillermet, L. Vallier, and E. Voisin	291
IN SITU HVEM STUDY OF ION IRRADIATION-INDUCED GRAIN GROWTH IN Au THIN FILMS Joyce C. Liu, Jian Li, J.W. Mayer, Charles W. Allen, and Lynn E. Rehn	297
PRECIPITATION OF Ar, Kr AND Xe IN Ni AT ROOM TEMPERATURE A.S. Liu and R.C. Birtcher	303
DEUTERIUM INTERACTIONS WITH ION-IMPLANTED OXYGEN IN Cu AND Au S.M. Myers, W.A. Swansiger, and D.M. Follstaedt	309
THE EFFECTS OF Ar-BOMBARDMENT ON THE DISSOLUTION AND REPRECIPITATION OF CARBONITRIDES IMPLANTED INTO LOW CARBON STEEL Stella M.M. Ramos, L. Amaral, M. Behar, A. Vasquez, and F.C. Zawislak	315
TEMPERATURE AND ORIENTATION EFFECTS IN IRON NITRIDE CRYSTAL FORMATION L.J. Lowder, W. Franzen, and R.J. Culbertson	321
PHASES AND MICROSTRUCTURES OF CARBON-IMPLANTED NIOBIUM J.S. Huang, R.G. Musket, and M.A. Wall	327

\*Invited Paper

PHASE STABILITY OF $Ni_2Al_3$ UNDER ELECTRON IRRADIATION E.A. Kenik and M. Nastasi	333
THE EFFECT OF SIMULTANEOUS ELECTRON AND $Kr^+$ IRRADIATION ON AMORPHIZATION OF CuTi J. Koike, P.R. Okamoto, L.E. Rehn, and M. Meshii	339
AMORPHIZATION OF $Zr_3Al$ BY HYDROGENATION AND SUBSEQUENT ELECTRON IRRADIATION W.J. Meng, J. Koike, P.R. Okamoto, and L.E. Rehn	345
RADIATION INDUCED AMORPHIZATION IN $YBa_2Cu_3O_7$ AND $GdBa_2Cu_3O_7$ SUPERCONDUCTORS Don M. Parkin and Michael Nastasi	351
STRUCTURAL MODIFICATIONS INDUCED BY THE ELECTRONIC SLOWING DOWN OF SWIFT HEAVY IONS IN MATTER J.C. Jousset, E. Balanzat, S. Bouffard, and M. Toulemonde	357
MICROSTRUCTURAL CHARACTERIZATION OF $Al_2O_3$ FOLLOWING SIMULTANEOUS TRIPLE ION BOMBARDMENT S.J. Zinkle	363
MICROSTRUCTURES IN $SiC$ AND $Si_3N_4$ IMPLANTED WITH Ti AND HEAT TREATED R.G. Vardiman	369
ION BEAM ANALYSIS OF O, N, AND B COMPOSITIONS IN MATERIALS USING NON-RUTHERFORD SCATTERING OF PROTONS N.R. Parikh, Z.H. Zhang, M.L. Swanson, N. Yu, and W.K. Chu	375
0.5 MeV SUBMICRON ION PROBE SYSTEM FOR RBS/PIXE K. Inoue, M. Takai, K. Ishibashi, Y. Kawata, N. Suzuki, and S. Namba	381
PART IV: PROPERTIES (TRIBOLOGICAL, OPTICAL, CHEMICAL)	
*TRIBOLOGY OF AMORPHOUS ALLOYS FORMED WITH ION BEAMS D.M. Follstaedt, J.A. Knapp, and L.E. Pope	389
ENHANCED WEAR RESISTANCE BY COMPRESSIVE STRENGTHENING A NOVEL COMBINATION OF LASER AND ION IMPLANTATION TECHNOLOGY H. de Beurs and J. Th. M. De Hosson	403
TRIBOLOGICAL AND MOSSBAUER STUDIES OF ION-IMPLANTED IRON D.L. Williamson, Yi Qu, Ronghua Wei, W.S. Sampath, and P.J. Wilbur	409
THE RELATIONSHIP BETWEEN CRYSTAL STRUCTURE AND HARDNESS OF NITROGEN IMPLANTED IRON SURFACE LAYERS Takanobu Fujihana, Yoshio Okabe, and Masaya Iwaki	415

\*Invited Paper

FRICITION CHARACTERISTICS OF B <sup>+</sup> - AND N <sub>2</sub> <sup>+</sup> -IMPLANTED Fe-Cr ALLOYS	421
Jun Sasaki and Masaya Iwaki	
THE CAUSES OF PROPERTY VARIATIONS OF IBAD-TITANIUM NITRIDE	427
R.A. Kant, S.A. Dillich, B.D. Sartwell, and J.A. Sprague	
CHARACTERIZATION OF TiN FILMS PREPARED BY ION BEAM ASSISTED DEPOSITION	433
Albert L. Chang and R.A. Kant	
THE FRICTION AND WEAR BEHAVIOR OF ION BEAM ASSISTED NITRIDE COATINGS	439
Thomas G. Tetreault, J.K. Hirvonen, G. Parker, and J.P. Hirvonen	
MICROSTRUCTURAL STUDIES OF IAD AND PVD Cr COATINGS BY CROSS SECTION TRANSMISSION ELECTRON MICROSCOPY	445
C.C. Cheng, R.A. Erck, and G.R. Fenske	
UNLUBRICATED SLIDING PROPERTIES OF ION BEAM AND EXCIMER LASER MIXED Fe-Ti-C MULTILAYERED FILMS	451
J-P. Hirvonen, M. Nastasi, T.R. Jervis, J.R. Tesmer, and T.G. Zocco	
SURFACE MECHANICAL PROPERTIES OF Ti ALLOYS PRODUCED BY EXCIMER LASER MIXING OF Ti ON AISI 304 STAINLESS STEEL	457
T.R. Jervis, J-P. Hirvonen, M. Nastasi, T.G. Zocco, J.A. Martin, G.M. Pharr, and W.C. Oliver	
COMBINED OXYGEN - NITROGEN ION IMPLANTS INTO Ti6Al4V	463
Anton Greenwald, James Daly, John Meroth, Richard Oliver, Piran Sioshansi, and Clive Clayton	
GROWTH OF STOICHIOMETRIC BN FILMS BY PULSED LASER EVAPORATION	469
P.T. Murray, M.S. Donley, and N.T. McDevitt	
EFFECTS OF ION BOMBARDMENT ON THE ENVIRONMENTAL DURABILITY OF SILVER COATINGS	475
G.A. Al-Jumaily, T.A. Mooney, and A. Smajkiewicz	
A STUDY OF THE ANODIC OXIDATION ON ALUMINIUM BY ION-IMPLANTED Xe IONS MARKER AND RBS ANALYSIS TECHNIQUES	479
Heming Chen, Xinde Bai, Wangpei Li, and Mingjiang Dai	
*ION BEAM PROCESSING OF OPTICAL MATERIALS	483
F.L. Williams, L.L. Boyer, D.W. Reicher, J.J. McNally, G.A. Al-Jumaily, and J.R. McNeil	
ION-ASSISTED DEPOSITION OF PROTECTIVE OVERLAYERS FOR MAGNETO-OPTIC ALLOYS	495
Kenneth D. Cornett, Ursula J. Gibson, and Anthony Taylor	

\*Invited Paper

THERMAL ANNEALING INVESTIGATION OF THE OPTICAL PROPERTIES OF $Si_{1-x}N_x$ FILMS FABRICATED BY ION BEAM ASSISTED DEPOSITION	501
E.P. Donovan, C.A. Carosella, and D. Van Vechten	
PASSIVATION OF GaAs LASER MIRRORS BY ION-BEAM DEPOSITED $Al_2O_3$	507
D.J. Webb, H.-P. Dietrich, F. Gfeller, A. Moser, and P. Vettiger	
EVALUATION OF MULTILAYERS FOR SOFT X-RAY FABRICATED BY ION BEAM SPUTTERING	513
I. Kataoka, I. Yamada, K. Eto, and K. Ito	
HIGH DOSE IMPLANTATION OF NITROGEN AND PHOSPHOR INTO SILICA GLASS	519
Takashi Tagami, Keiji Oyoshi, and Shuhei Tanaka	
MICROTOPOGRAPHY OF ION BEAM ETCHED $NiP$ FILMS	525
Kazuhiko Noguchi, Ryuzi Ueda, Yoshitaka Maeyama, Shigeo Sasaki, and Kazumichi Machida	
PART V: ELECTRONIC MATERIALS	
*ION-BEAM-INDUCED EPITAXY AND SOLUTE SEGREGATION AT THE Si CRYSTAL-AMORPHOUS INTERFACE	533
J.M. Poate, D.C. Jacobson, F. Priolo, and Michael O. Thompson	
SEGREGATION OF Ag AND Cu DURING ION BEAM AND THERMALLY INDUCED RECRYSTALLIZATION OF AMORPHOUS SI	545
J.S. Custer, Michael O. Thompson, and J.M. Poate	
STUDY OF ENHANCED SOLID PHASE EPITAXY OF AMORPHOUS SILICON WITH LOW CONCENTRATIONS OF IMPLANTED PHOSPHOROUS	551
Young-Jin Jeon, Won Woo Park, M.F. Becker, and Rodger M. Walser	
INFLUENCE OF PHOSPHORUS DOPANT CONCENTRATION ON RECRYSTALLIZATION OF BURIED AMORPHOUS LAYERS IN Si(100) PRODUCED BY CHANNELED IMPLANTS	557
R.J. Schreutelkamp, K.T.F. Janssen, F.W. Saris, J.F.M. Westendorp, and R.E. Kaim	
ION-ASSISTED REGROWTH OF DEPOSITED Si LAYERS MECHANISMS AND MORPHOLOGY	563
F. Priolo, C. Spinella, A. La Ferla, A. Battaglia, E. Rimini, G. Ferla, A. Carnera, and A. Gasparotto	
SELF ANNEALING IMPLANTATION OF $As^+$ IN SILICON	569
M. Berti, A.V. Drigo, R. Lotti, G. Lulli, and P.G. Merli	
ION BEAM SELF ANNEALING IN THIN SILICON FILMS	575
J.D. Rubio, R.P. Vijay, R.R. Hart, and J.D. Pearce	

\*Invited Paper

INFLUENCE OF THE IMPLANTED SPECIES ON THE RESIDUAL DAMAGE AFTER HOT IMPLANTS IN SILICON	581
L. Calcagno, C. Spinella, M. Catania, S.U. Campisano, G. Foti, G. Ferla, and E. Rimini	
FURNACE ANNEAL OF a-AXIS SAPPHIRE AMORPHISED BY INDIUM ION IMPLANTATION	587
D.K. Sood and D.X. Cao	
DAMAGE FORMATION IN SEMICONDUCTORS DURING MeV ION IMPLANTATION	593
T.P. Sjoreen, O.W. Holland, M.K. El-Ghor, and C.W. White	
ELECTRICAL ACTIVATION OF HEAVILY DOPED ARSENIC IMPLANTED SILICON	599
J. Said, H. Jaouen, G. Ghibaudo, I. Stoemenos, and P. Zaumseil	
RADIATION DAMAGE OF SiO <sub>2</sub> /Si BY ENERGETIC NEUTRAL BEAM AND VUV PHOTONS	605
Tatsumi Mizutani, Shigeru Nishimatsu, and Takashi Yunogami	
A COMPARISON OF LOW ENERGY BF <sub>2</sub> IMPLANTATION IN Si AND Ge PREAMORPHIZED SILICON	611
Gary A. Ruggles, Shin-Nam Hong, Jimmie J. Wortman, Mehmet Ozturk, Edward R. Myers, John J. Hren, and Richard B. Fair	
ION IMPLANTATION DOPING OF SIMOX WITH <sup>31</sup> P AND <sup>69</sup> Ga	617
K.S. Jones, D. Venables, C.R. Horne, and G. Davis	
LOW-DEFECT, HIGH-QUALITY SIMOX PRODUCED BY MULTIPLE OXYGEN IMPLANTATION WITH SUBSTOICHIOMETRIC TOTAL DOSE	623
F. Namavar, E. Cortesi, and P. Sioshansi	
INFLUENCE OF ION-IMPLANTATION ON CHARACTERISTICS OF PICOSECOND PHOTOCONDUCTIVE SWITCHES	629
John F. Knudsen, Robert C. Bowman, Jr., Duane D. Smith, and Steven C. Moss	
FORMATION OF SHALLOW BORON P <sup>+</sup> JUNCTIONS USING Sb AMORPHIZATION	635
E. Ganin, B. Davari, D. Harame, G. Scilla, and G.A. Sai-Halasz	
SILICIDED SHALLOW JUNCTION FORMATION USING ION IMPLANTATION AND THERMAL ANNEALING	641
Leonard M. Rubin, N. Herbots, D. Hoffman, and D. Ma	
ON THE STRUCTURE, COMPOSITION, AND I-V CHARACTERISTICS OF Al/Ti:W/a-Si CONTACTS	647
S. Berger and Y. Komem	



SYNTHESIS OF TWO-LAYER TiB <sub>2</sub> -TiSi <sub>2</sub> STRUCTURES BY BORON IMPLANTATION INTO TITANIUM FILM AND RAPID THERMAL ANNEALING	653
V.V. Tokarev, A.I. Demchenko, A.I. Ivanov, V.E. Borisenko, and D.I. Zarovsky	
SYNTHESIS OF TRANSITION METAL EPITAXIAL SILICIDES ON SILICON (100), (111)	659
V.V. Tokarev, V.E. Borisenko, and T.M. Pyatkova	
ATOMIC PROFILES AND ELECTRICAL CHARACTERISTICS OF VERY HIGH ENERGY (8-20 MeV) Si IMPLANTS IN GaAs	665
Phillip E. Thompson, Harry B. Dietrich, James M. Eridon, and Thomas Gresko	
INTERBAND OPTICAL PROPERTIES OF THE MICROCRYSTALLINE COMPONENT WITHIN THE DAMAGE LAYER OF Be <sup>+</sup> -IMPLANTED GaAs	671
G.F. Feng and R. Zallen	
CHARACTERISTICS OF Si-IMPLANTED (211) VERSUS (100) GaAs	677
J. Epp, J.G. Dillard, A. Siochi, R. Zallen, E.D. Cole, S. Sen, A. Vaseashta, and L.C. Burton	
ABOUT SOME PECULIARITIES IN DEFECT APPEARANCE IN ELEMENTAL AND III-V COMPOUND SEMICONDUCTING MATERIALS	683
Maria G. Kalitzova, N.K. Pashov, G. Vitali, and M. Rossi	
ION ENERGY AND DOSE EFFECTS DURING ION-ASSISTED EPITAXIAL GROWTH OF InAs ON Si(100)	689
C.-H. Choi and S.A. Barnett	
ION BOMBARDMENT EFFECTS ON GaAs USING 100eV NITROGEN IONS	695
W.M. Lau	
THIN FILMS OF p-TYPE CdTe GROWN WITH ION-BEAM-ASSISTED DOPING	701
Paul Sharps, Alan L. Fahrenbruch, Adolfo Lopez-Otero, and Richard H. Bube	
ION IMPLANTATION OF BORON IN DIAMOND	707
G.S. Sandhu, M.L. Swanson, and W.K. Chu	
ION IMPLANTATION AND ION BEAM ANALYSIS OF LITHIUM NIOBATE	713
G.W. Arnold	
ION IMPLANTATION OF KNbO <sub>3</sub> AND LiNbO <sub>3</sub> AT ELEVATED TEMPERATURES	719
Ch. Buchal, R. Irscher, and P. Günter	
EFFECT OF MICROSTRUCTURE ON THE SHEET RESISTANCE OF ION-BEAM DEPOSITED ZnO THIN FILM	725
Saliman A. Isa, P.K. Ghosh, and P.G. Kornreich	

EFFECT OF ION BOMBARDMENT ON THE DOPANT DIFFUSION DURING REACTIVE ION ETCHING (RIE) OF DIELECTRIC FILMS DEPOSITED ON SILICON	731
K. Shenai, N. Lewis, G.A. Smith, and B.J. Baliga	
ELECTRICALLY CONDUCTING THIN FILMS BY ION IMPLANTATION OF PYROLYZED POLYACRYLONITRILE	737
R.A. Basheer	
MICRO-RBS ANALYSIS OF MASKLESSLY FABRICATED STRUCTURES	743
A. Kinomura, M. Takai, T. Matsuo, M. Satou, M. Kiuchi, K. Fujii, and S. Namba	
DEPTH PROFILING OF ION BEAM INDUCED DAMAGE IN SEMICONDUCTOR HETEROSTRUCTURES	749
R. Germann, A. Forchel, G. Hörcher, and G. Weimann	
AUTHOR INDEX	755
SUBJECT INDEX	759